Silicon NPN Power Transistors 2SC1626

DESCRIPTION

·With TO-220C package
·Complement to type 2SA816

APPLICATIONS

·Designed for the driver stages of 30-50W high-fidelity amplifiers and medium speed switching up to 2A peak current

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

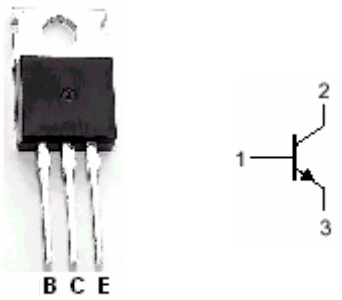

Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	80	V
V_{CEO}	Collector-emitter voltage	Open base	80	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		750	mA
I_{CM}	Collector current-peak		2	A
P_T	Total power dissipation	T_a=25□	1.5	W
		T_C=25□	10	
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-50~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=10mA ; I_B=0	80			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=0.1mA ; I_E=0	80			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=500mA; I_B=50mA			0.5	V
V_{BE}	Base-emitter on voltage	I_C=500m A ; V_{CE}=2V			1.0	V
I_{CBO}	Collector cut-off current	V_{CB}=30V ;I_E=0			0.5	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			1	μA
h_{FE-1}	DC current gain	I_C=150m A ; V_{CE}=2V	70		240	
h_{FE-2}	DC current gain	I_C=500m A ; V_{CE}=2V	40			
f_T	Transition frequency	I_C=150m A ; V_{CE}=2V	50			MHz
C_{ob}	Collector output capacitance	I_E=0;f=1MHz ; V_{CB}=10V		13		pF

◆ **h_{FE-1} Classifications**

O	Y
70-140	120-240

PACKAGE OUTLINE

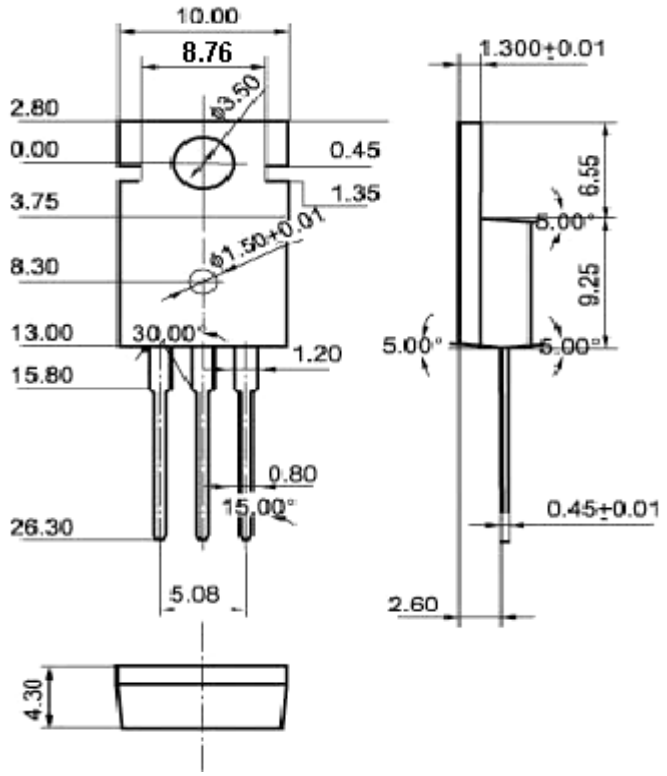

Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)